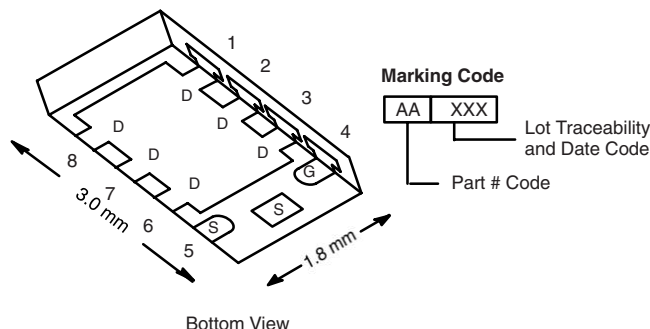


## N-Channel 60-V (D-S) MOSFET

### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) <sup>a</sup> | $Q_g$ (Typ.) |
|--------------|---------------------------|------------------------|--------------|
| 60           | 0.034 at $V_{GS} = 10$ V  | 12                     | 10.5 nC      |
|              | 0.041 at $V_{GS} = 4.5$ V | 12                     |              |

PowerPAK ChipFET Single



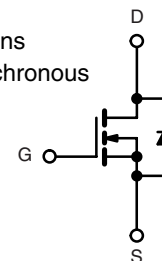
### FEATURES

- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFET
- New Thermally Enhanced PowerPAK<sup>®</sup> ChipFET<sup>®</sup> Package
  - Small Footprint Area
  - Low On-Resistance
  - Thin 0.8 mm Profile


RoHS  
COMPLIANT

### APPLICATIONS

- Load Switch for Portable Applications
- DC-DC Switch for Low Power Synchronous Rectification
- Intermediate Switch Driver for DC/DC Applications



Ordering Information: Si5476DU-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ , unless otherwise noted

| Parameter                                                    | Symbol         | Limit                    | Unit             |
|--------------------------------------------------------------|----------------|--------------------------|------------------|
| Drain-Source Voltage                                         | $V_{DS}$       | 60                       | V                |
| Gate-Source Voltage                                          | $V_{GS}$       | $\pm 20$                 |                  |
| Continuous Drain Current ( $T_J = 150^\circ\text{C}$ )       | $I_D$          | $T_C = 25^\circ\text{C}$ | A                |
|                                                              |                | $T_C = 70^\circ\text{C}$ |                  |
|                                                              |                | $T_A = 25^\circ\text{C}$ |                  |
|                                                              |                | $T_A = 70^\circ\text{C}$ |                  |
| Pulsed Drain Current                                         | $I_{DM}$       | 25                       | A                |
| Continuous Source-Drain Diode Current                        | $I_S$          | $T_C = 25^\circ\text{C}$ |                  |
|                                                              |                | $T_A = 25^\circ\text{C}$ |                  |
| Avalanche Current                                            | $I_{AS}$       | 15                       | mJ               |
| Single Pulse Avalanche Energy                                | $E_{AS}$       | 11.2                     |                  |
| Maximum Power Dissipation                                    | $P_D$          | $T_C = 25^\circ\text{C}$ | W                |
|                                                              |                | $T_C = 70^\circ\text{C}$ |                  |
|                                                              |                | $T_A = 25^\circ\text{C}$ |                  |
|                                                              |                | $T_A = 70^\circ\text{C}$ |                  |
| Operating Junction and Storage Temperature Range             | $T_J, T_{stg}$ | - 55 to 150              | $^\circ\text{C}$ |
| Soldering Recommendations (Peak Temperature) <sup>d, e</sup> |                | 260                      |                  |

### THERMAL RESISTANCE RATINGS

| Parameter                                   | Symbol     | Typical | Maximum | Unit               |
|---------------------------------------------|------------|---------|---------|--------------------|
| Maximum Junction-to-Ambient <sup>b, f</sup> | $R_{thJA}$ | 34      | 40      | $^\circ\text{C/W}$ |
| Maximum Junction-to-Case (Drain)            | $R_{thJC}$ | 3       | 4       |                    |

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c.  $t = 5$  s.

d. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is  $90^\circ\text{C/W}$ .

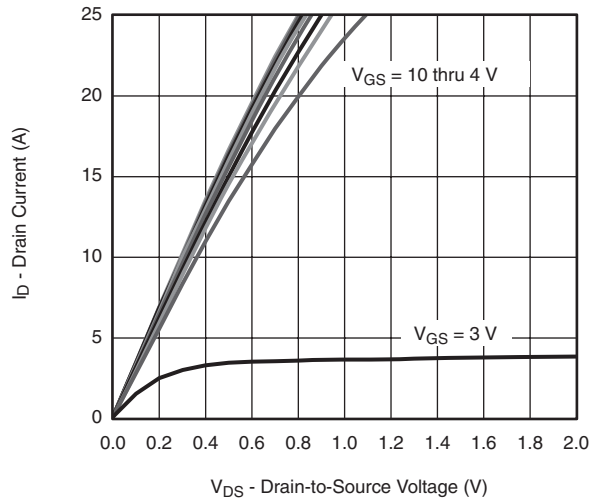
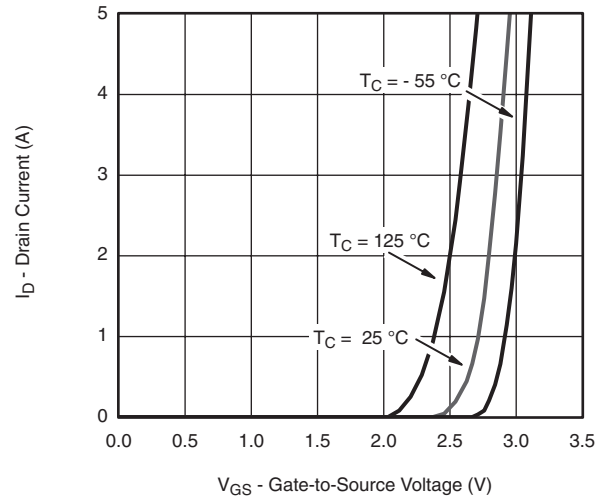
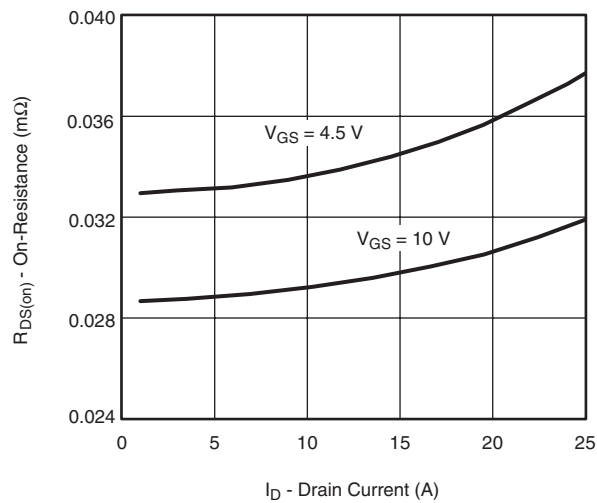
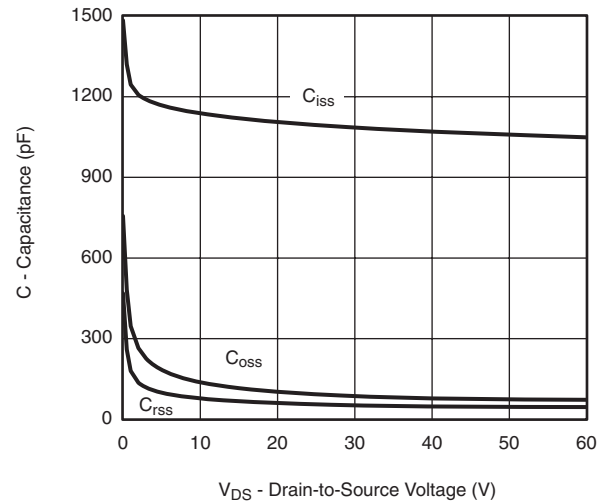
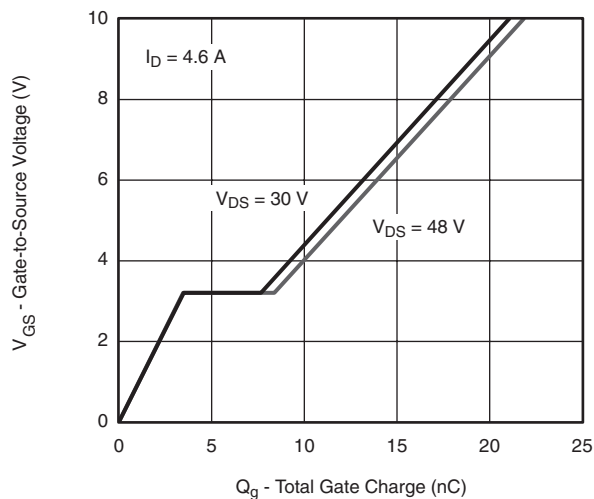
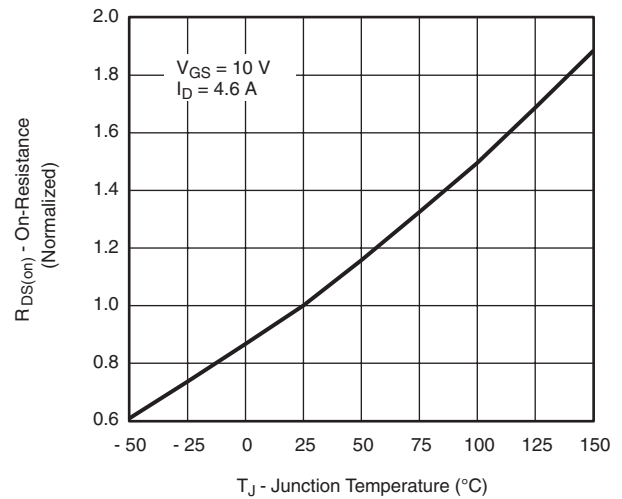
| SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted |                                      |                                                                                                                          |      |       |       |       |
|---------------------------------------------------------------|--------------------------------------|--------------------------------------------------------------------------------------------------------------------------|------|-------|-------|-------|
| Parameter                                                     | Symbol                               | Test Conditions                                                                                                          | Min. | Typ.  | Max.  | Unit  |
| Static                                                        |                                      |                                                                                                                          |      |       |       |       |
| Drain-Source Breakdown Voltage                                | V <sub>DS</sub>                      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA                                                                             | 60   |       |       | V     |
| V <sub>DS</sub> Temperature Coefficient                       | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = 250 μA                                                                                                  |      | 55    |       | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient                   | ΔV <sub>GS(th)</sub> /T <sub>J</sub> |                                                                                                                          |      | - 6.3 |       |       |
| Gate-Source Threshold Voltage                                 | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                              | 1    |       | 3     | V     |
| Gate-Source Leakage                                           | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                          |      |       | ± 100 | nA    |
| Zero Gate Voltage Drain Current                               | I <sub>DSS</sub>                     | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V                                                                            |      |       | 1     | μA    |
|                                                               |                                      | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                    |      |       | 10    |       |
| On-State Drain Current <sup>a</sup>                           | I <sub>D(on)</sub>                   | V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V                                                                            | 25   |       |       | A     |
| Drain-Source On-State Resistance <sup>a</sup>                 | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.6 A                                                                           |      | 0.028 | 0.034 | Ω     |
|                                                               |                                      | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 4.2 A                                                                          |      | 0.033 | 0.041 |       |
| Forward Transconductance <sup>a</sup>                         | g <sub>fs</sub>                      | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.6 A                                                                           |      | 20    |       | S     |
| Dynamic <sup>b</sup>                                          |                                      |                                                                                                                          |      |       |       |       |
| Input Capacitance                                             | C <sub>iss</sub>                     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                                 |      | 1100  |       | pF    |
| Output Capacitance                                            | C <sub>oss</sub>                     |                                                                                                                          |      | 90    |       |       |
| Reverse Transfer Capacitance                                  | C <sub>rss</sub>                     |                                                                                                                          |      | 55    |       |       |
| Total Gate Charge                                             | Q <sub>g</sub>                       | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.6 A                                                   |      | 21    | 32    | nC    |
|                                                               |                                      | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 4.6 A                                                  |      | 10.5  | 16    |       |
| Gate-Source Charge                                            | Q <sub>gs</sub>                      |                                                                                                                          |      | 3.5   |       |       |
| Gate-Drain Charge                                             | Q <sub>gd</sub>                      |                                                                                                                          |      | 4.2   |       |       |
| Gate Resistance                                               | R <sub>g</sub>                       | f = 1 MHz                                                                                                                |      | 3.3   |       | Ω     |
| Turn-On Delay Time                                            | t <sub>d(on)</sub>                   | V <sub>DD</sub> = 30 V, R <sub>L</sub> = 5.4 Ω<br>I <sub>D</sub> ≅ 5.6 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω |      | 20    | 30    | ns    |
| Rise Time                                                     | t <sub>r</sub>                       |                                                                                                                          |      | 150   | 225   |       |
| Turn-Off Delay Time                                           | t <sub>d(off)</sub>                  |                                                                                                                          |      | 20    | 30    |       |
| Fall Time                                                     | t <sub>f</sub>                       |                                                                                                                          |      | 60    | 90    |       |
| Turn-On Delay Time                                            | t <sub>d(on)</sub>                   | V <sub>DD</sub> = 30 V, R <sub>L</sub> = 5.4 Ω<br>I <sub>D</sub> ≅ 5.6 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω  |      | 10    | 15    |       |
| Rise Time                                                     | t <sub>r</sub>                       |                                                                                                                          |      | 15    | 25    |       |
| Turn-Off Delay Time                                           | t <sub>d(off)</sub>                  |                                                                                                                          |      | 22    | 40    |       |
| Fall Time                                                     | t <sub>f</sub>                       |                                                                                                                          |      | 10    | 15    |       |
| Drain-Source Body Diode Characteristics                       |                                      |                                                                                                                          |      |       |       |       |
| Continuous Source-Drain Diode Current                         | I <sub>S</sub>                       | T <sub>C</sub> = 25 °C                                                                                                   |      |       | 12    | A     |
| Pulse Diode Forward Current                                   | I <sub>SM</sub>                      |                                                                                                                          |      |       | 25    |       |
| Body Diode Voltage                                            | V <sub>SD</sub>                      | I <sub>S</sub> = 5.5 A, V <sub>GS</sub> = 0 V                                                                            |      | 0.85  | 1.2   | V     |
| Body Diode Reverse Recovery Time                              | t <sub>rr</sub>                      | I <sub>F</sub> = 5.5 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C                                                         |      | 25    | 50    | ns    |
| Body Diode Reverse Recovery Charge                            | Q <sub>rr</sub>                      |                                                                                                                          |      | 25    | 50    | nC    |
| Reverse Recovery Fall Time                                    | t <sub>a</sub>                       |                                                                                                                          |      | 19    |       | ns    |
| Reverse Recovery Rise Time                                    | t <sub>b</sub>                       |                                                                                                                          |      | 6     |       |       |

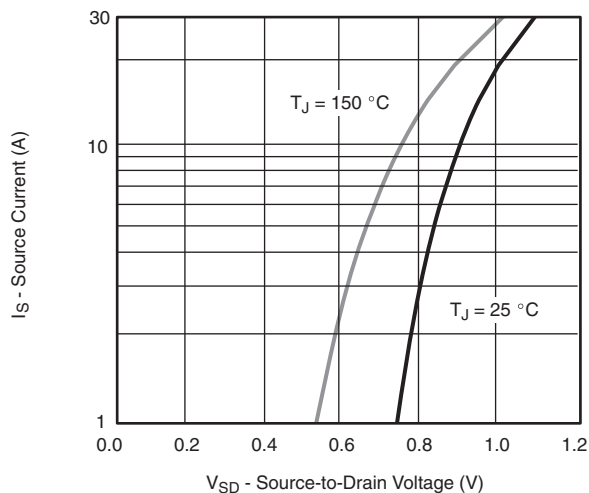
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

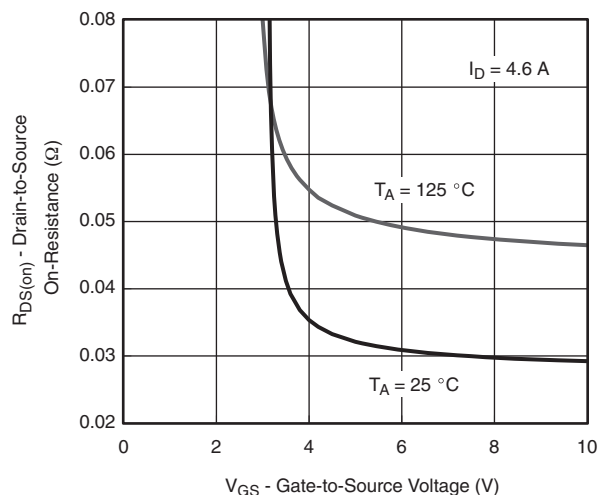
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

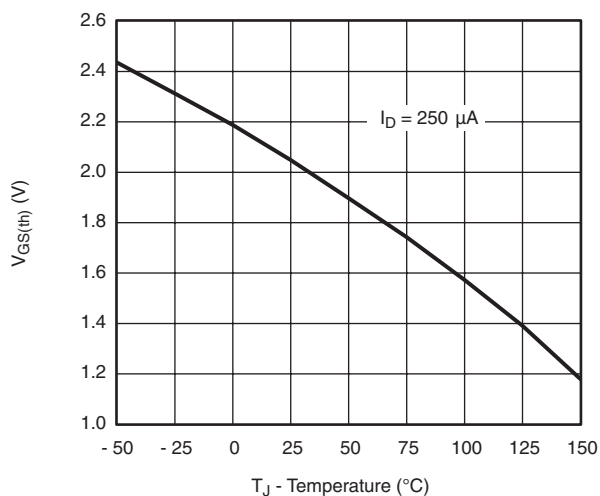
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current and Gate Voltage****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

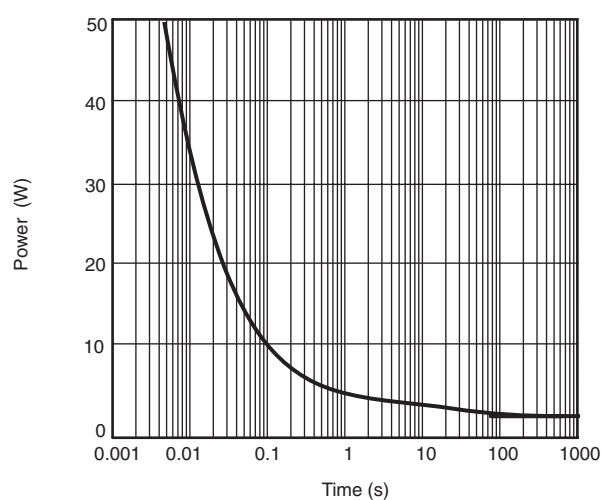
Source-Drain Diode Forward Voltage



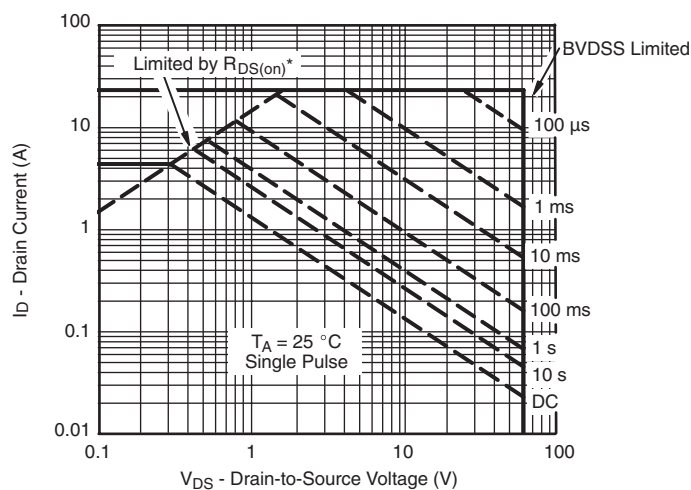
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



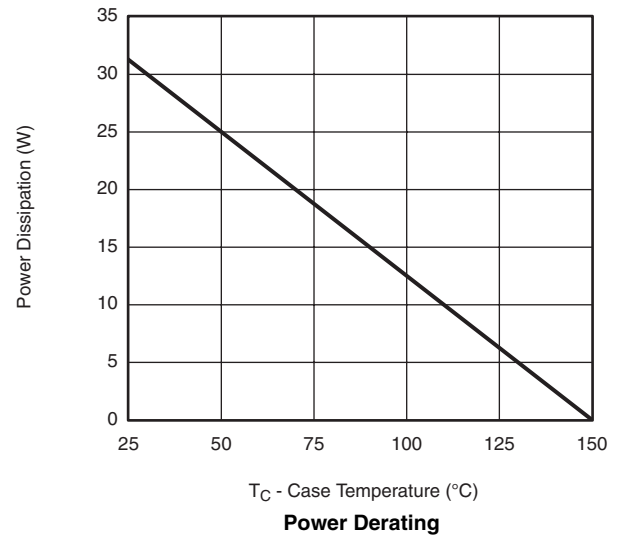
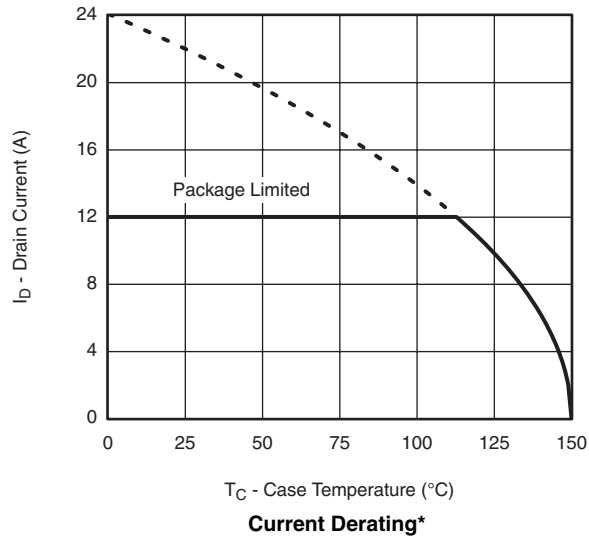
Single Pulse Power, Junction-to-Ambient

\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

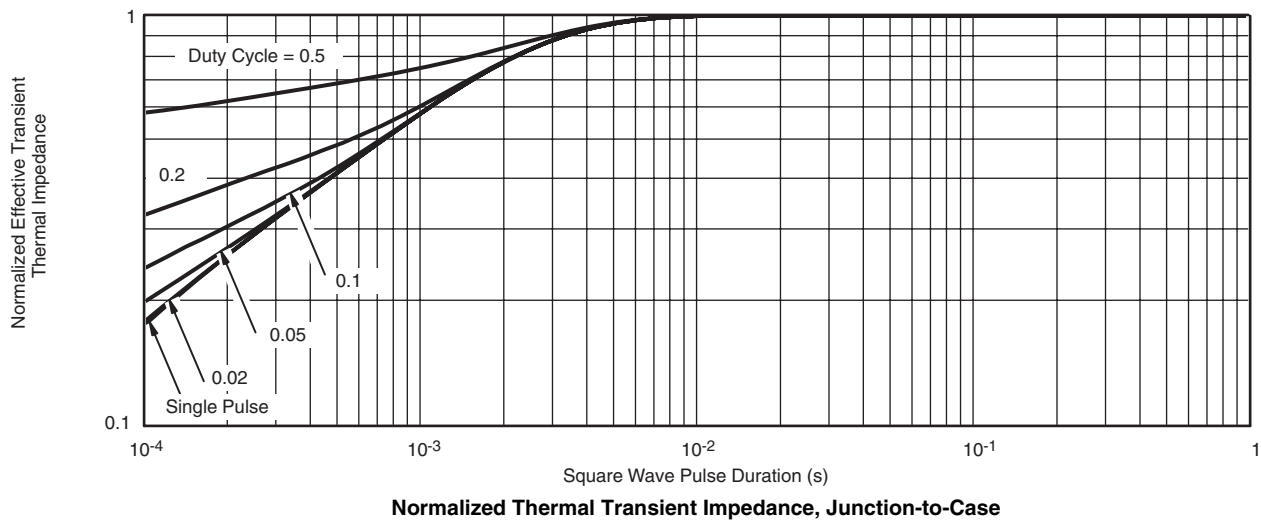
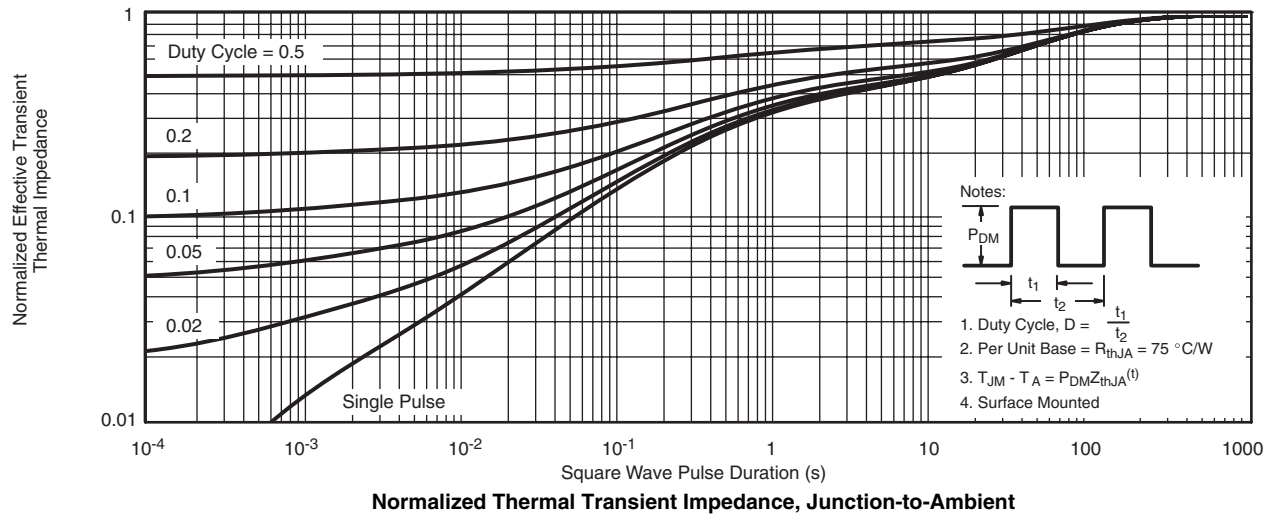
Safe Operating Area, Junction-to-Ambient



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

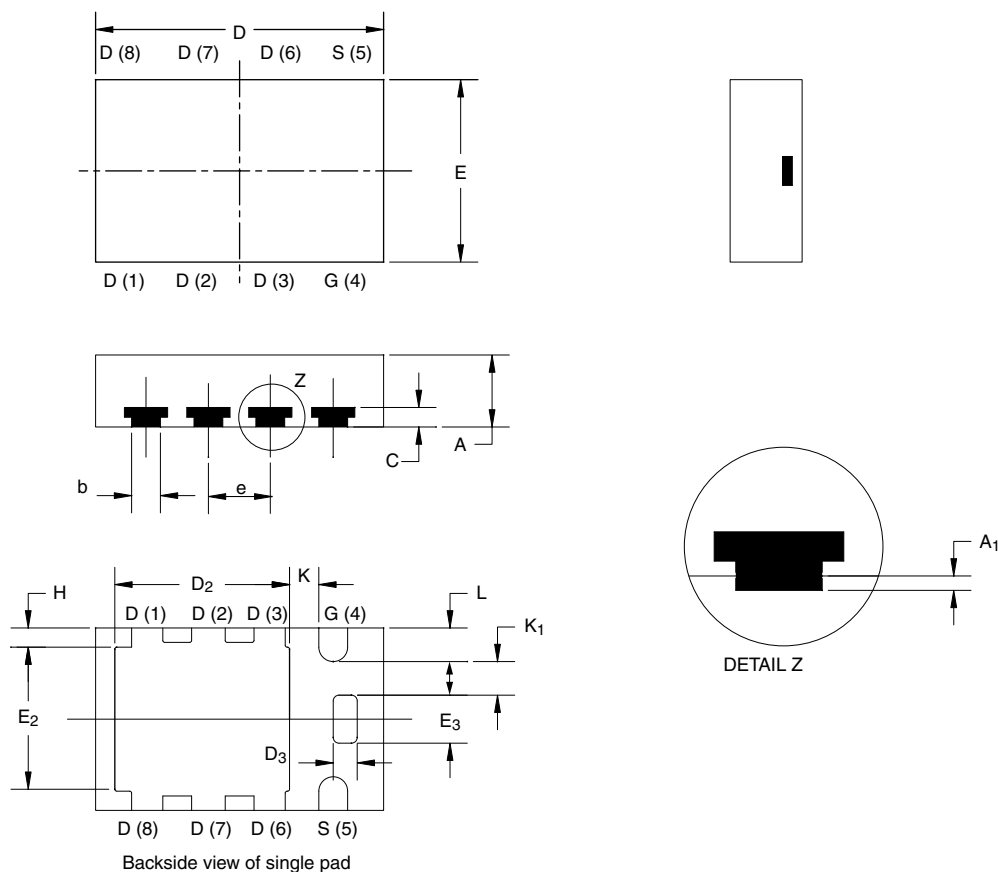


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

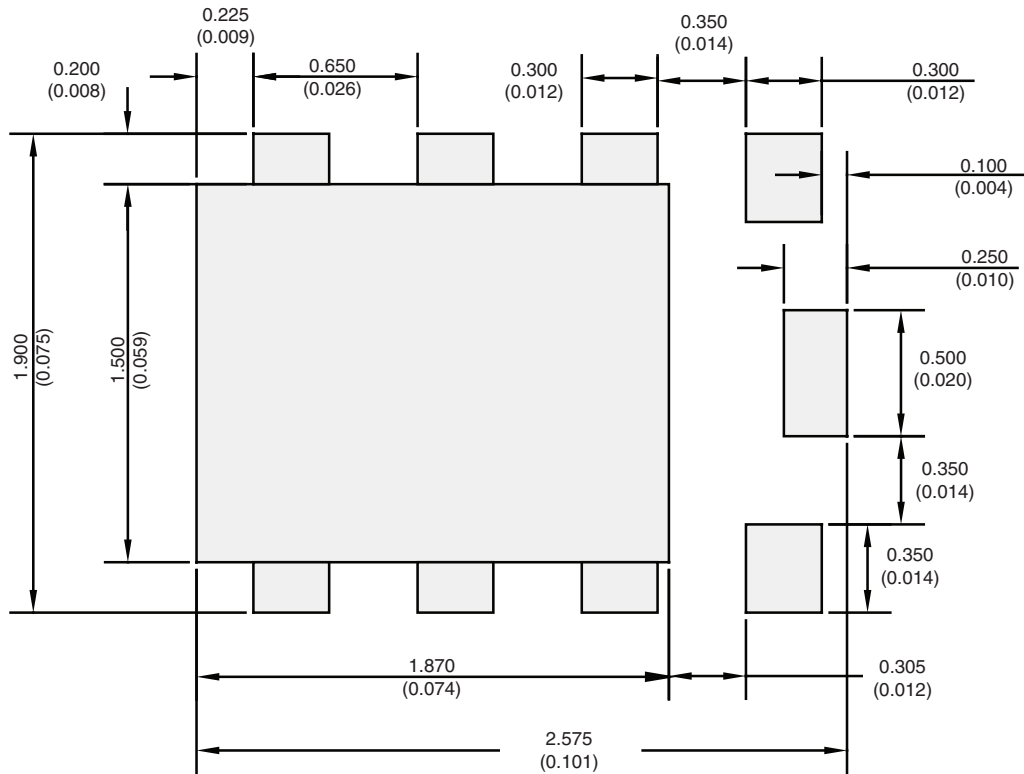
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73663>.

## PowerPAK® ChipFET® SINGLE PAD



| DIM.           | MILLIMETERS |      |      | INCHES    |       |       |
|----------------|-------------|------|------|-----------|-------|-------|
|                | MIN.        | NOM. | MAX. | MIN.      | NOM.  | MAX.  |
| A              | 0.70        | 0.75 | 0.85 | 0.028     | 0.030 | 0.033 |
| A <sub>1</sub> | 0           | -    | 0.05 | 0         | -     | 0.002 |
| b              | 0.25        | 0.30 | 0.35 | 0.010     | 0.012 | 0.014 |
| C              | 0.15        | 0.20 | 0.25 | 0.006     | 0.008 | 0.010 |
| D              | 2.92        | 3.00 | 3.08 | 0.115     | 0.118 | 0.121 |
| D <sub>2</sub> | 1.75        | 1.87 | 2.00 | 0.069     | 0.074 | 0.079 |
| D <sub>3</sub> | 0.20        | 0.25 | 0.30 | 0.008     | 0.010 | 0.012 |
| E              | 1.82        | 1.90 | 1.98 | 0.072     | 0.075 | 0.078 |
| E <sub>2</sub> | 1.38        | 1.50 | 1.63 | 0.054     | 0.059 | 0.064 |
| E <sub>3</sub> | 0.45        | 0.50 | 0.55 | 0.018     | 0.020 | 0.022 |
| e              | 0.65 BSC    |      |      | 0.026 BSC |       |       |
| H              | 0.15        | 0.20 | 0.25 | 0.006     | 0.008 | 0.010 |
| K              | 0.25        | -    | -    | 0.010     | -     | -     |
| K <sub>1</sub> | 0.30        | -    | -    | 0.012     | -     | -     |
| L              | 0.30        | 0.35 | 0.40 | 0.012     | 0.014 | 0.016 |

## RECOMMENDED MINIMUM PADS FOR PowerPAK® ChipFET® Single



Recommended Minimum Pads  
Dimensions in mm/(Inches)

[Return to Index](#)





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